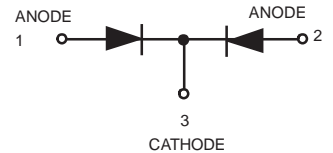
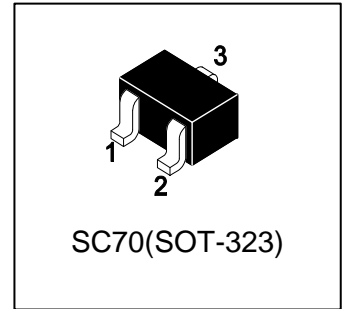


LDAN202UT1G

S-LDAN202UT1G

Dual Serise Switching Diodes



1. FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

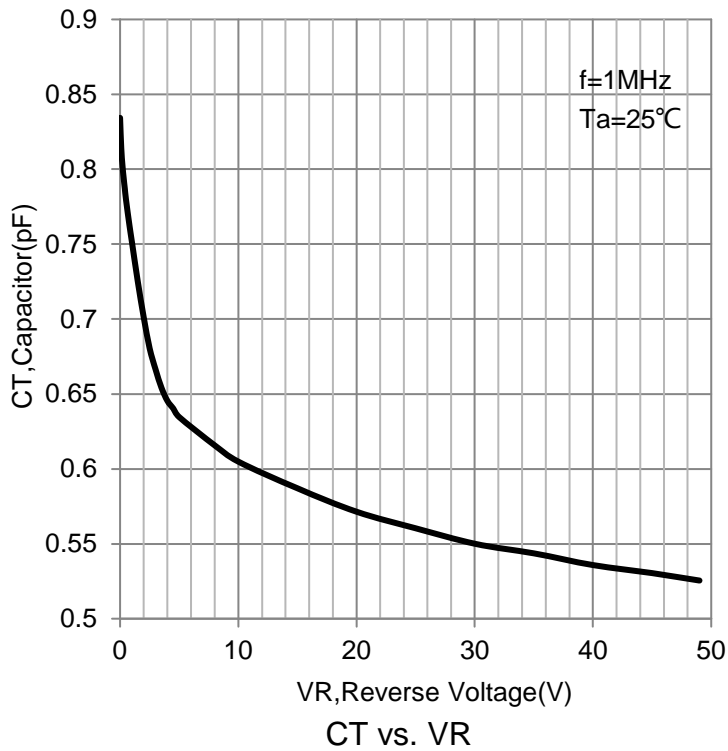
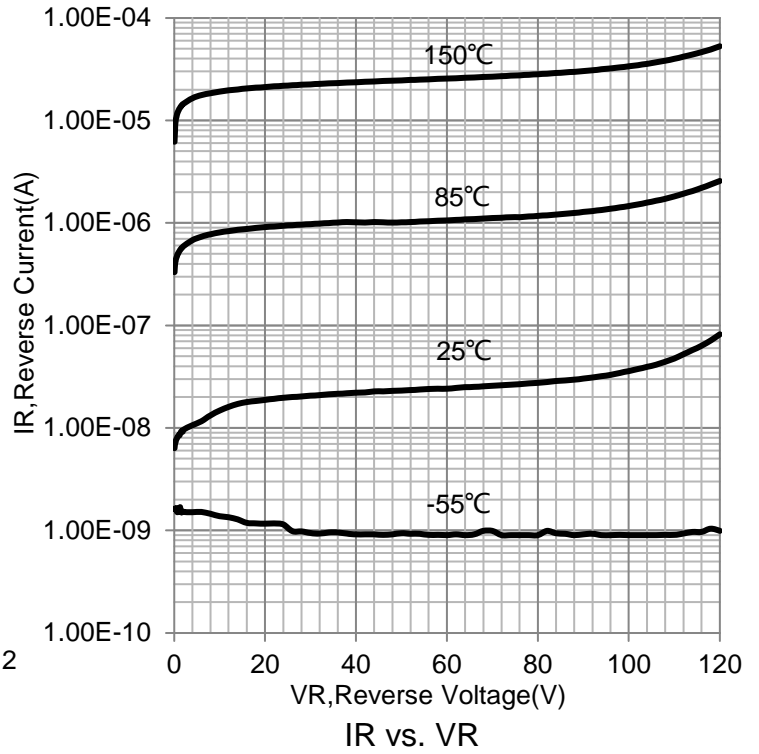
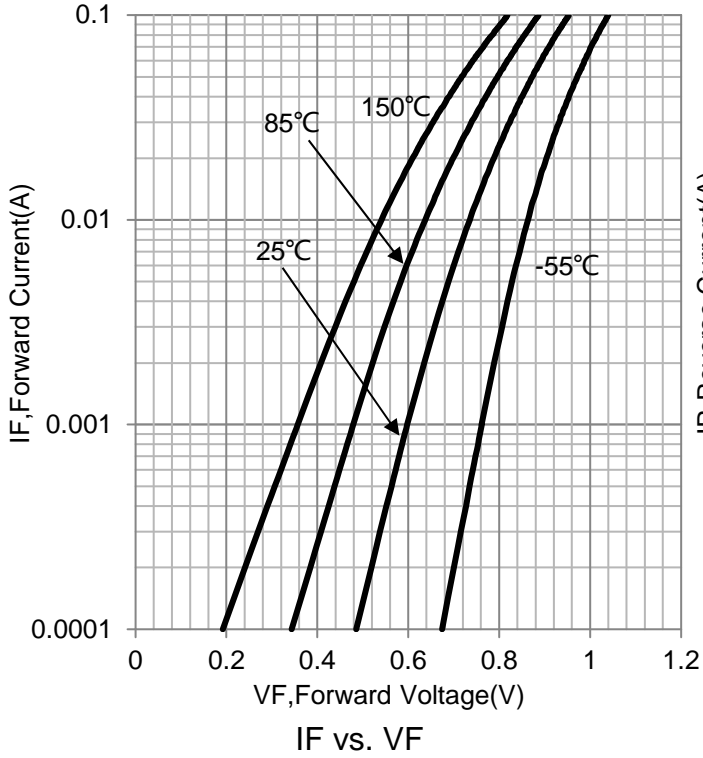
2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LDAN202UT1G	N	3000/Tape&Reel
LDAN202UT3G	N	10000/Tape&Reel

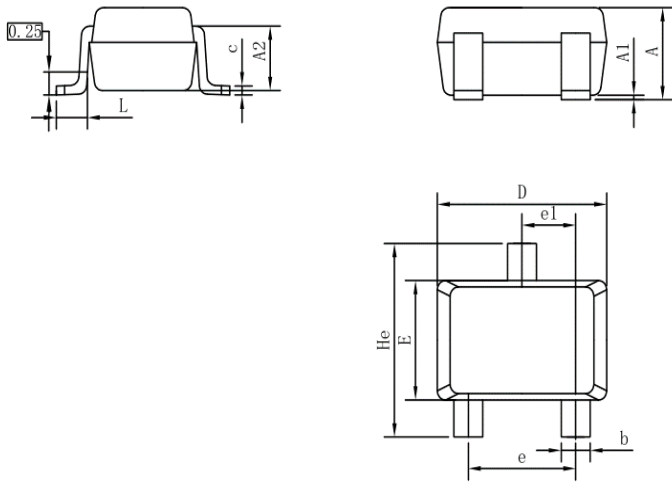
3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse Voltage	VR	80	V
Forward Current	IO	100	mA
Peak Forward Surge Current	IFSM	300	mA
Forward voltage (If = 100mA)	VF	1.2	V
Reverse current (Vr = 70V)	IR	0.1	μA
Capacitance between terminals(f =1MHz)	CT	3.5	pF
Reverse recovery time(Vr= 6V,If=5 mA)	Trr	4	nS

4.ELECTRICAL CHARACTERISTICS CURVES

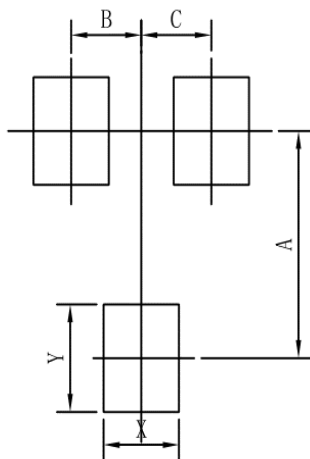


5.OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

6.SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90